(12) **United States Patent**
Baker

(10) **Patent No.:** **US 7,082,045 B2**
(45) **Date of Patent:** **Jul. 25, 2006**

(54) **OFFSET COMPENSATED SENSING FOR MAGNETIC RANDOM ACCESS MEMORY**

(75) Inventor: **R. Jacob Baker**, Boise, ID (US)

(73) Assignee: **Micron Technology, Inc.**, Boise, ID (US)

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

(21) Appl. No.: **11/133,236**

(22) Filed: **May 20, 2005**

(65) **Prior Publication Data**

US 2005/0219928 A1 Oct. 6, 2005

Related U.S. Application Data

(62) Division of application No. 10/828,162, filed on Apr. 21, 2004, now Pat. No. 6,917,534, which is a division of application No. 10/422,850, filed on Apr. 25, 2003, now Pat. No. 6,856,532, which is a division of application No. 09/938,722, filed on Aug. 27, 2001, now Pat. No. 6,597,600.

(51) **Int. Cl.**
G11C 17/02 (2006.01)

(52) **U.S. Cl.** **365/97**; 365/100; 365/158; 365/207

(58) **Field of Classification Search** 365/97, 365/207, 205, 100, 158
See application file for complete search history.

(56) **References Cited**

U.S. PATENT DOCUMENTS

|			
6,166,944 A	12/2000	Ogino	
6,188,615 B1 *	2/2001	Perner et al.	365/97
6,262,625 B1	7/2001	Perner et al.	
6,388,917 B1	5/2002	Hoffman et al.	
6,396,733 B1	5/2002	Lu et al.	
6,462,600 B1 *	10/2002	Pakriswamy	327/307
6,650,562 B1	11/2003	Holden et al.	

* cited by examiner

Primary Examiner—Huan Hoang
(74) *Attorney, Agent, or Firm*—Dickstein Shapiro Morin & Oshinsky LLP

(57) **ABSTRACT**

An offset compensated memory element voltage supply including a differential amplifier with a compensation circuit, and a transistor with a gate connected to the output of the differential amplifier. The compensation circuit of the differential amplifier includes a compensation capacitor that stores a compensation voltage during a calibration phase, and applies the stored compensation voltage to a compensation input of the compensation circuit of the amplifier during a measurement phase. Feedback from a source of the transistor controls the output of the differential amplifier to maintain a standard voltage across a resistive memory element connected to the source during measurement of the resistance of the resistive memory element, and the compensation circuit improves the accuracy of the voltage across the resistive memory element by compensating for an offset voltage of the differential amplifier.

8 Claims, 11 Drawing Sheets
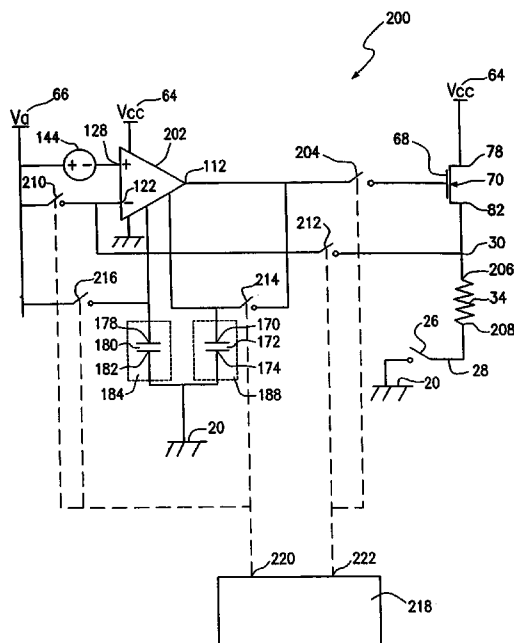
FIG. 1
(PRIOR ART)
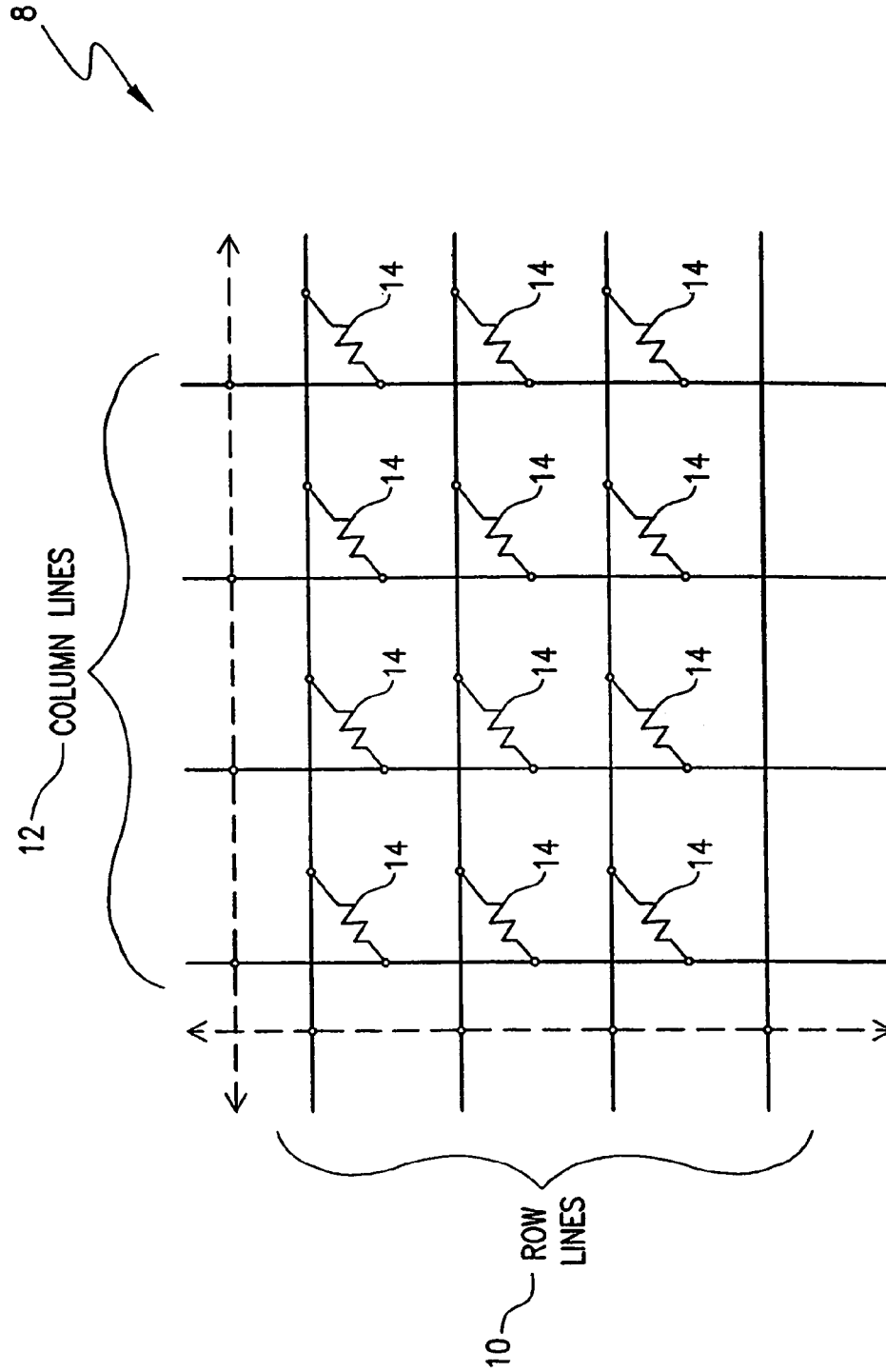
FIG. 2
(PRIOR ART)

FIG. 3
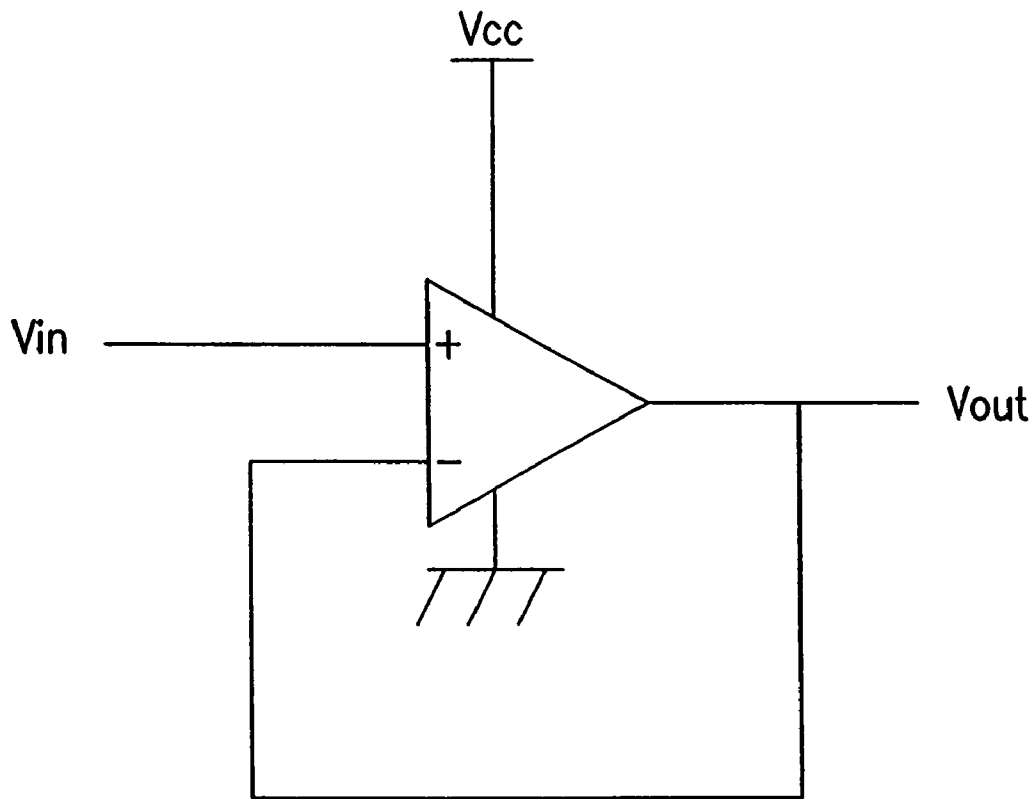
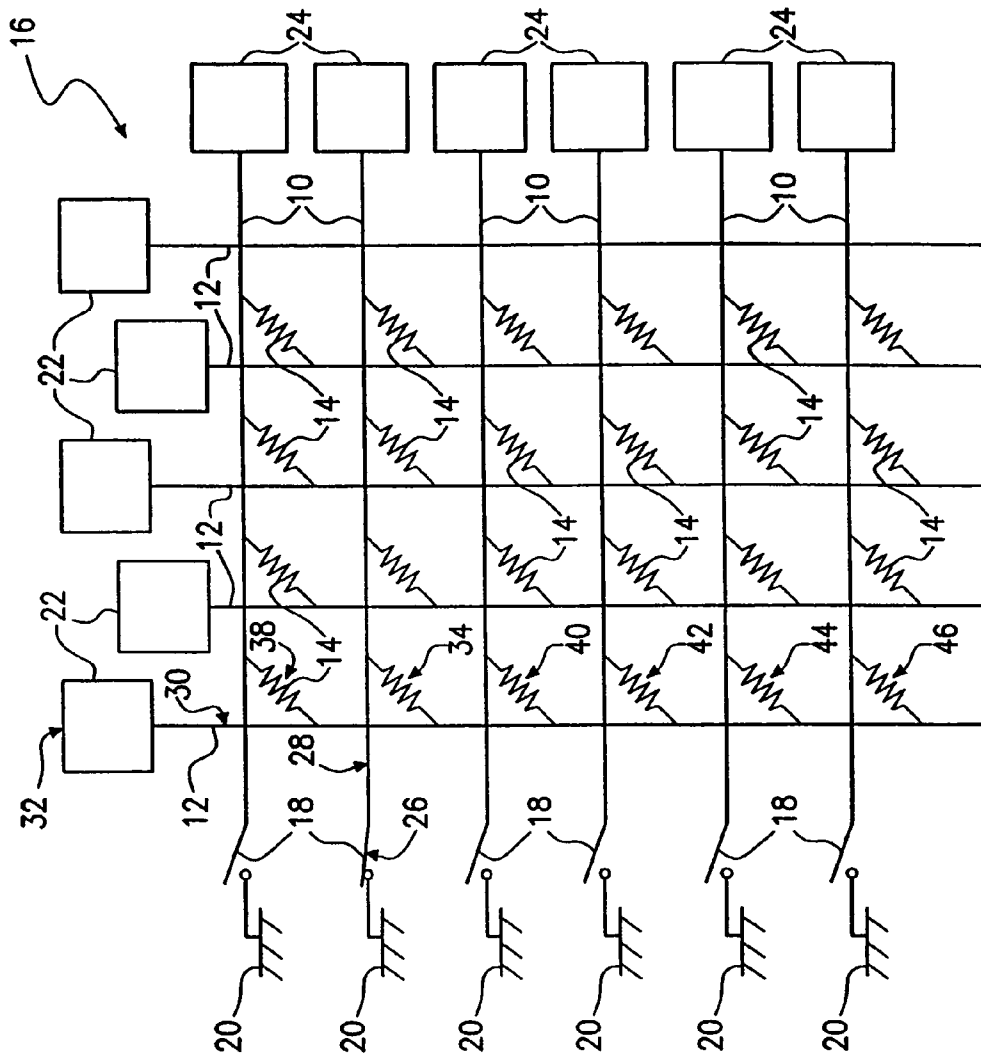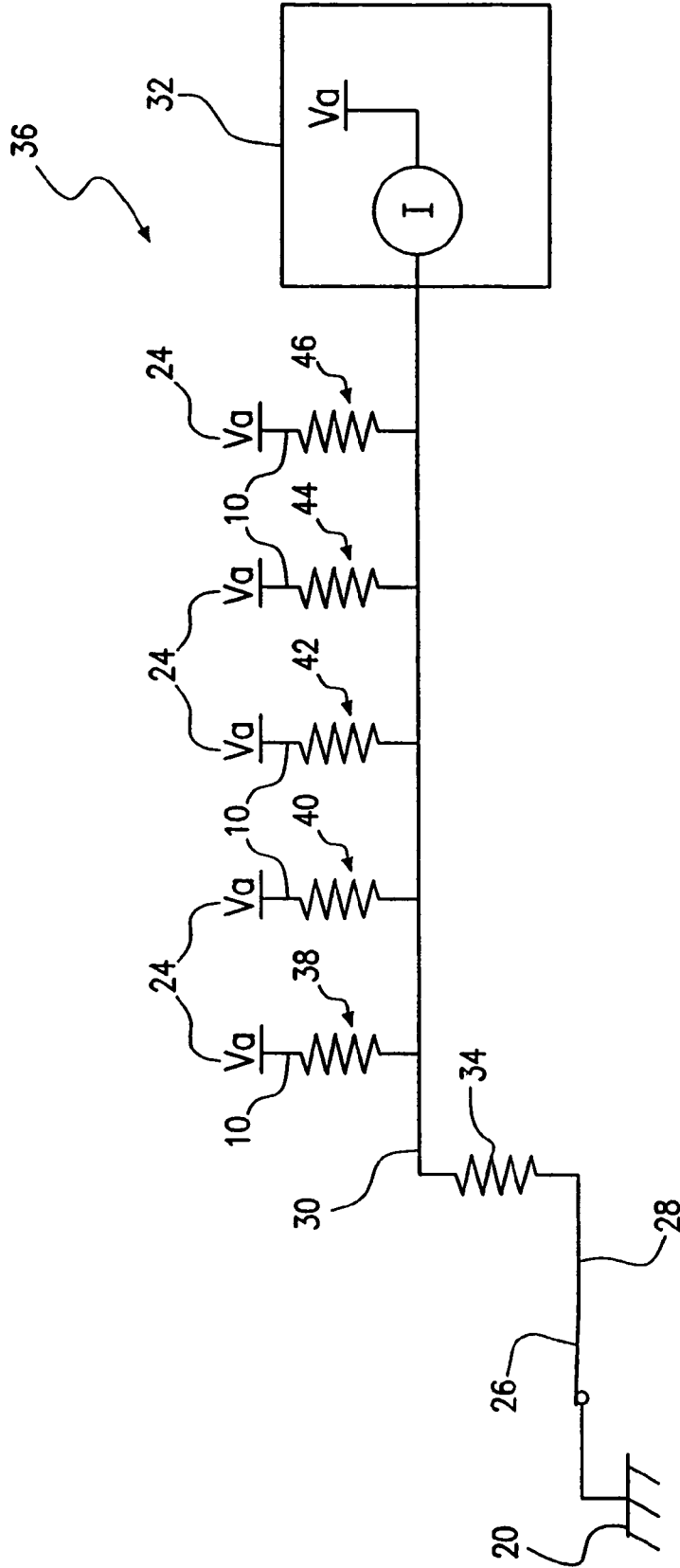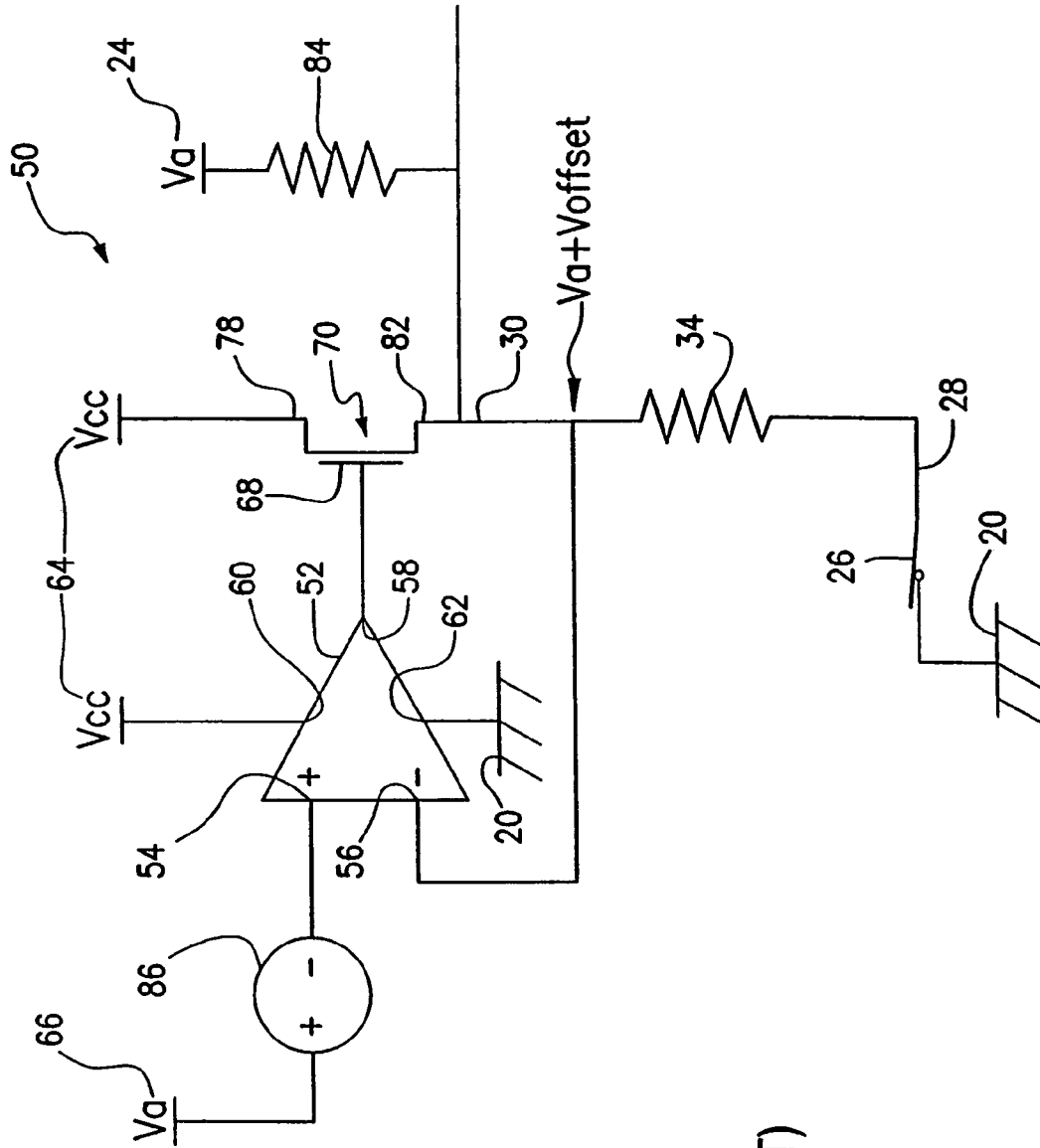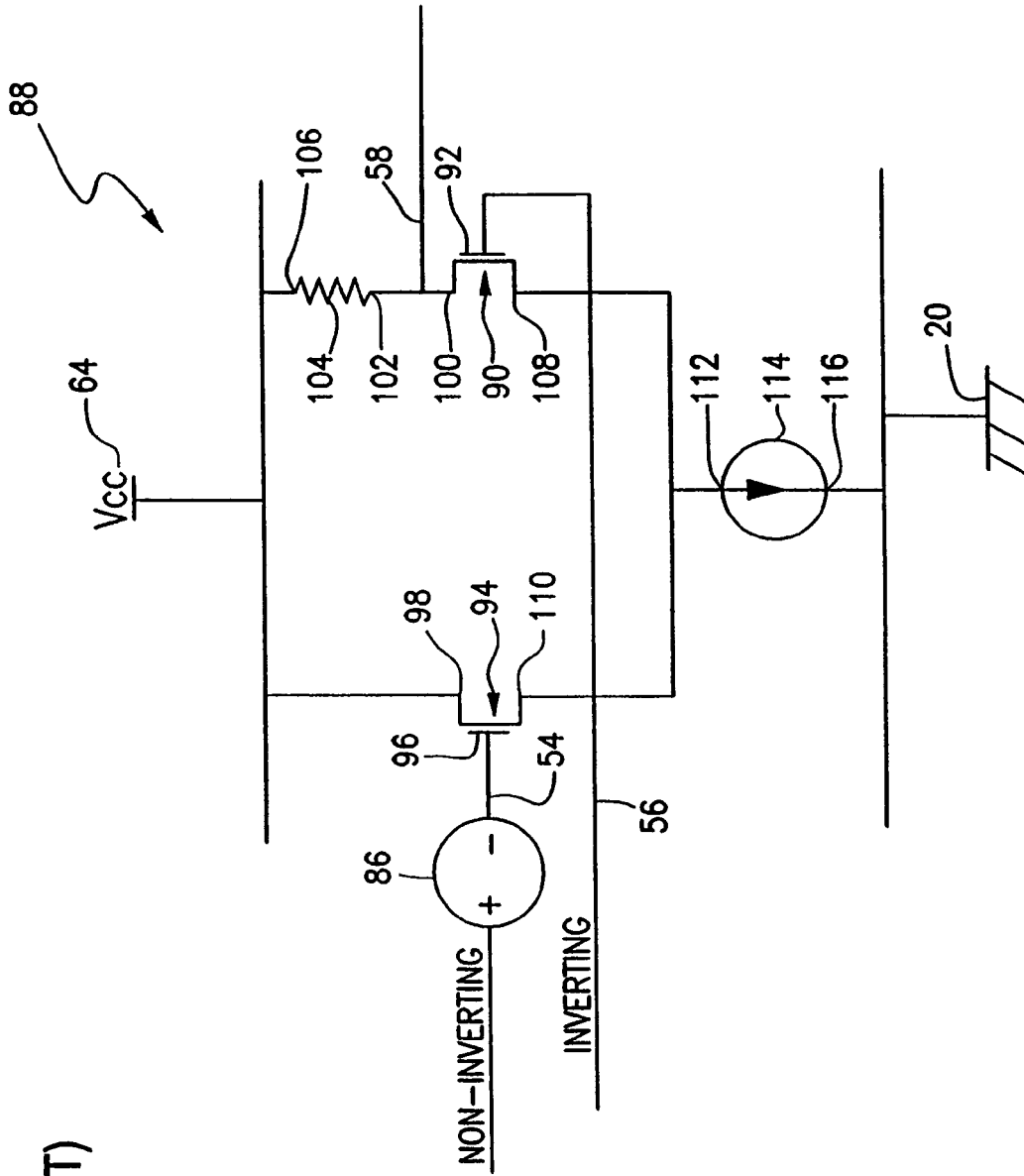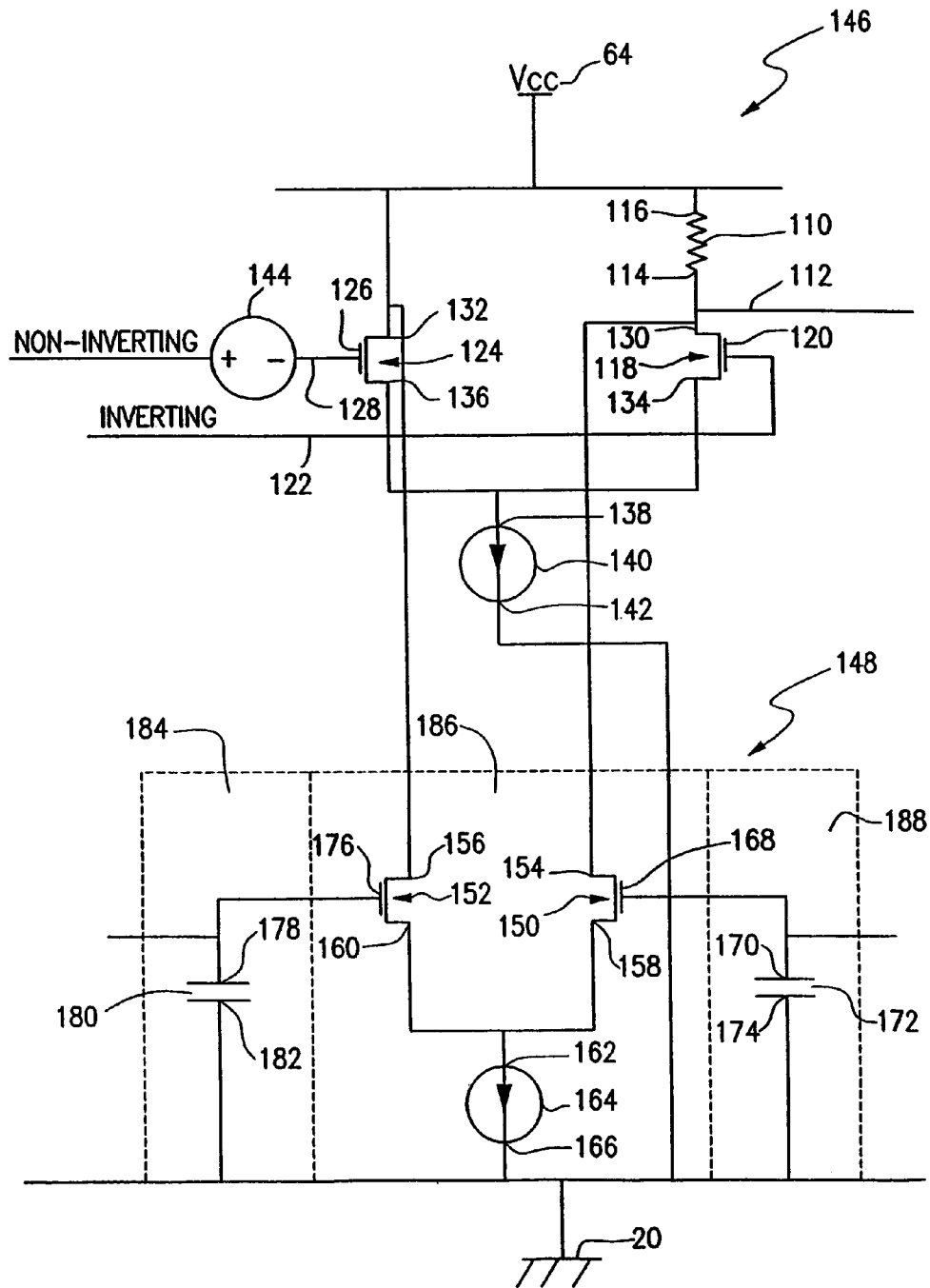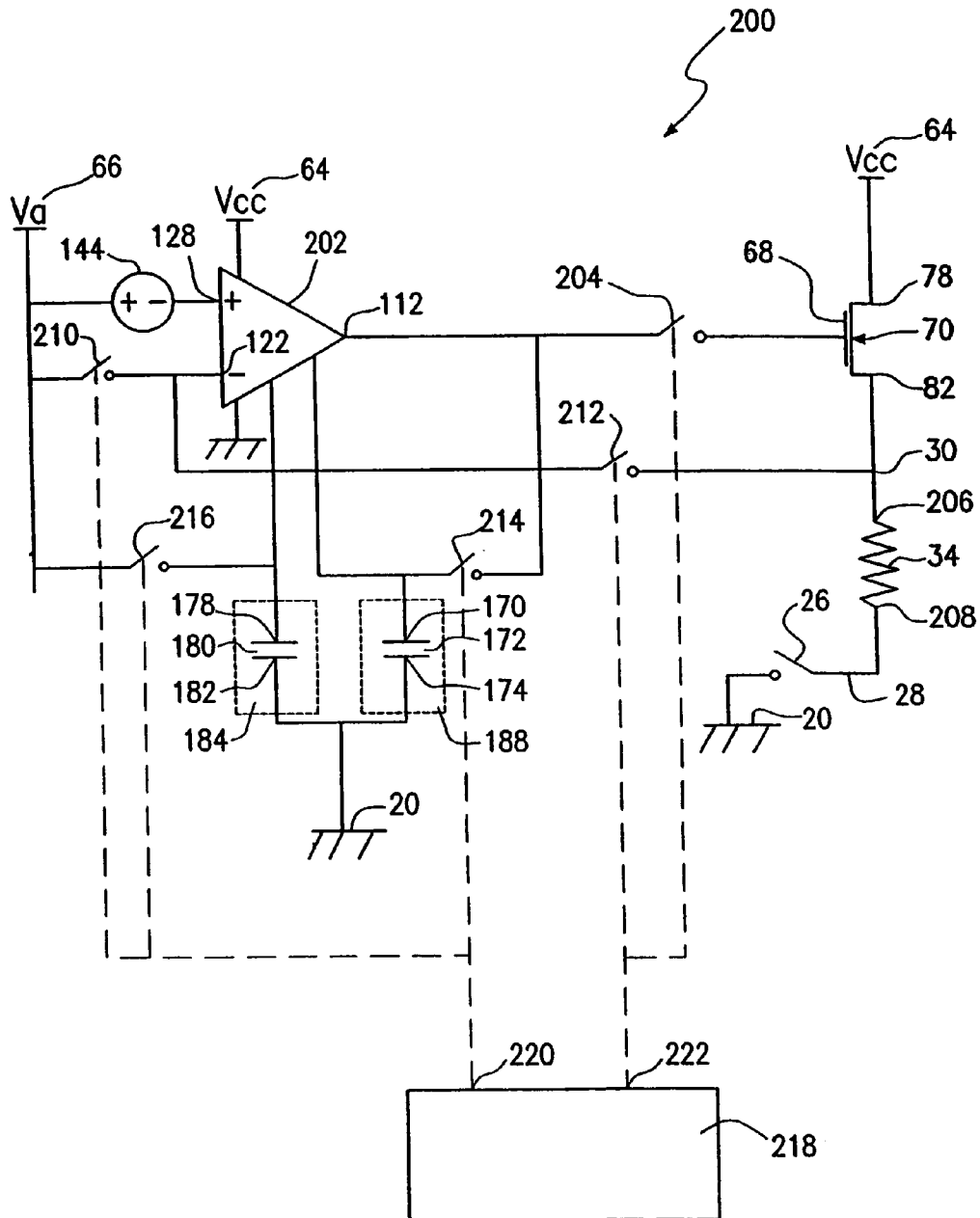*FIG. 4*

FIG. 5
(PRIOR ART)

FIG. 6
(PRIOR ART)

FIG. 7

FIG. 8

FIG. 9

FIG. 10

FIG. 11

230

CPU

234

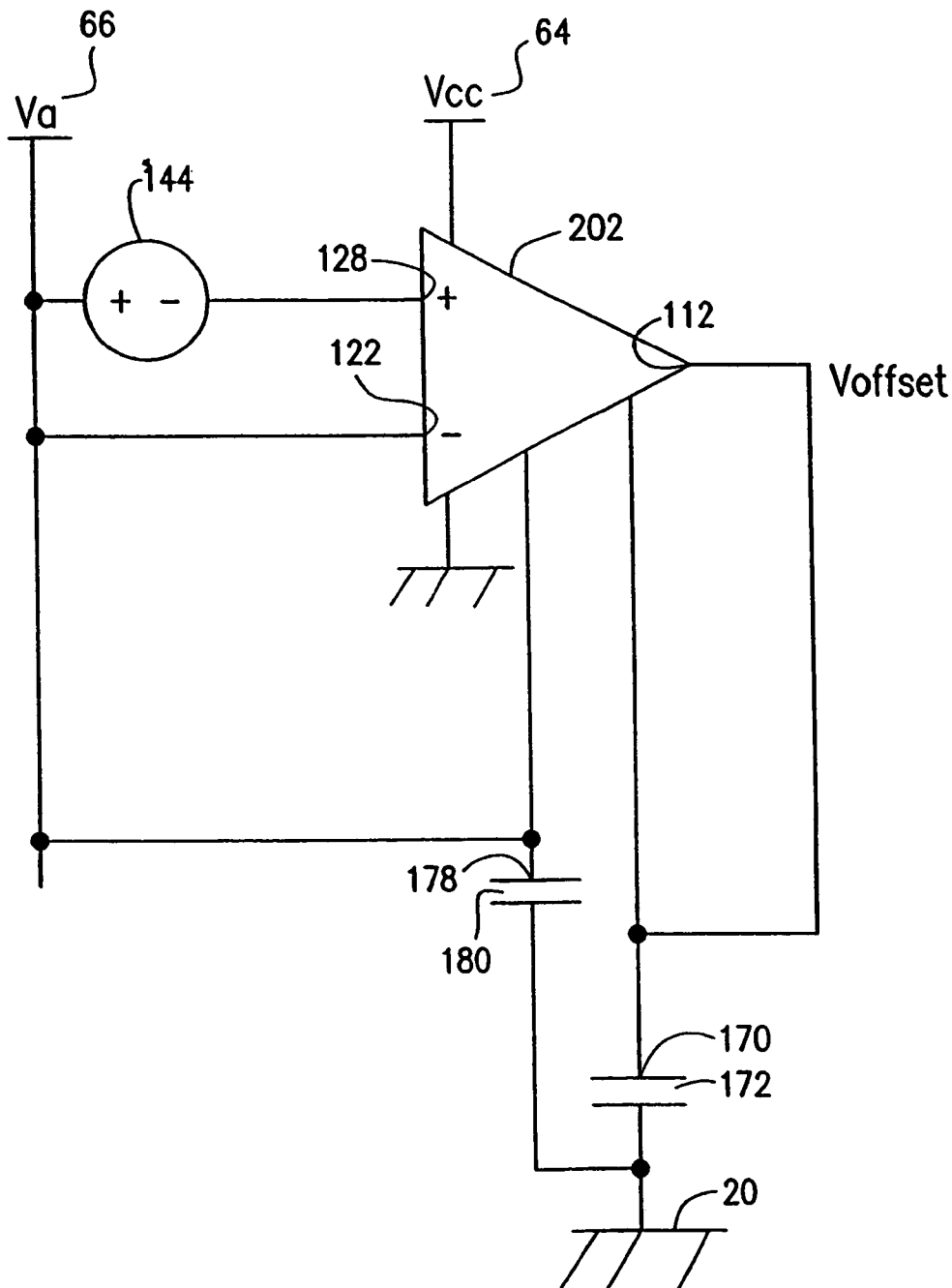DIGITAL
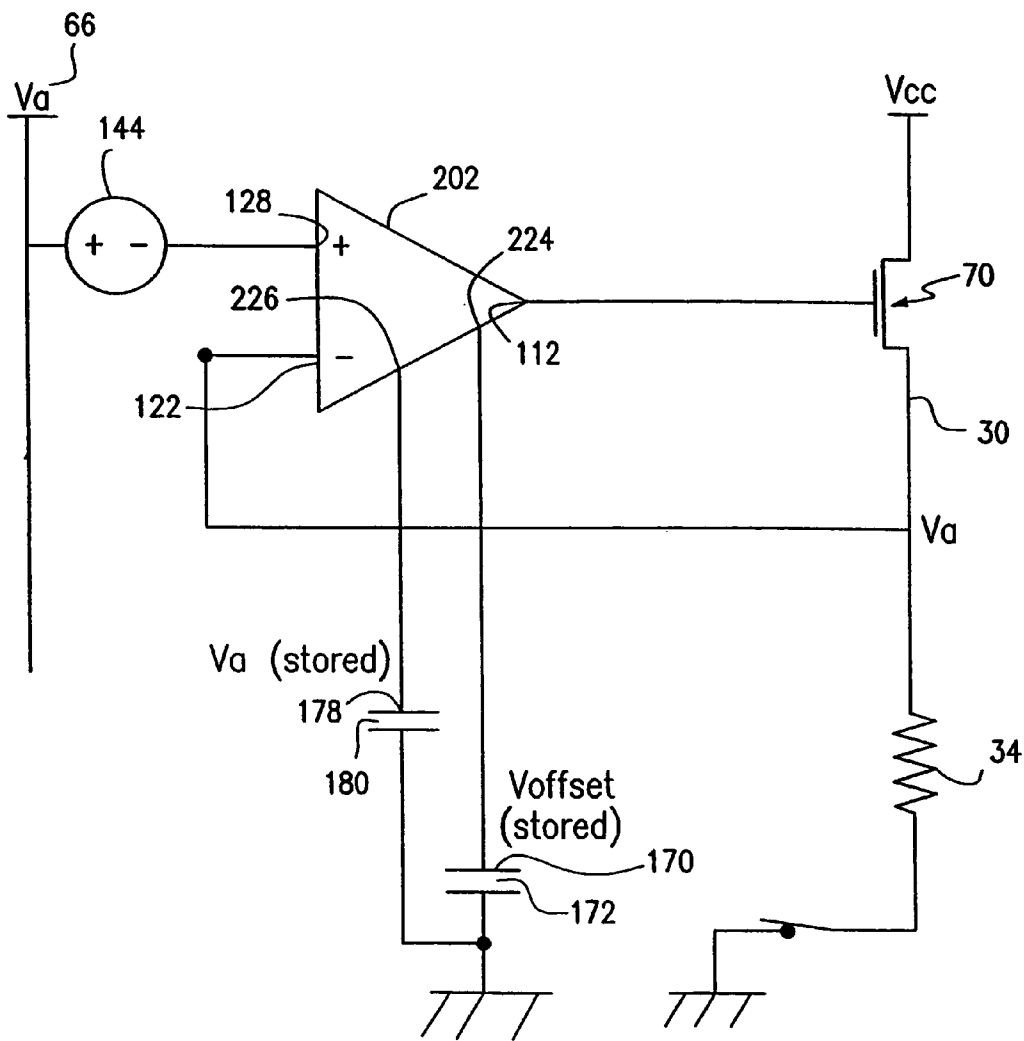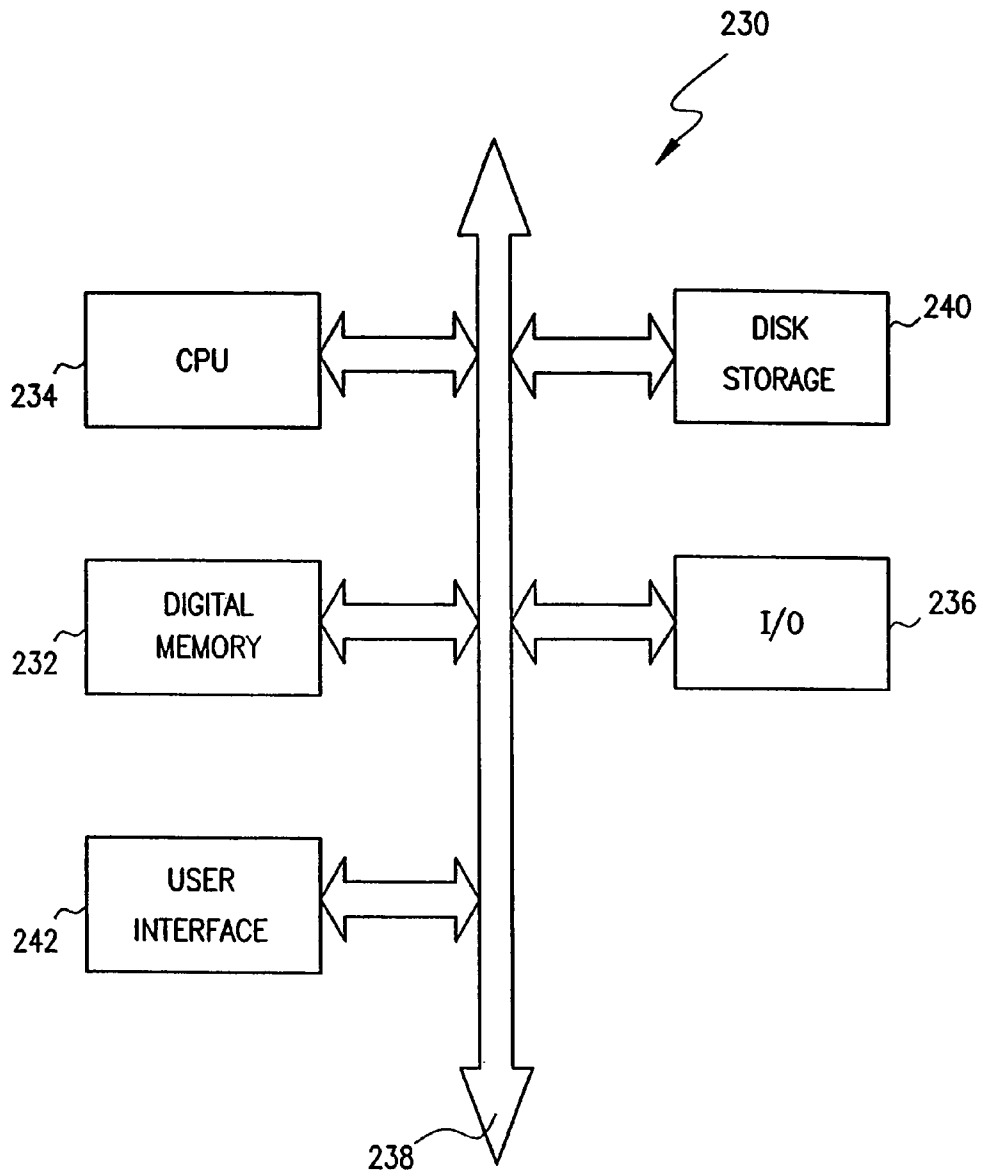MEMORY

232

USER
INTERFACE

242

DISK
STORAGE

240

I/O

236

238

OFFSET COMPENSATED SENSING FOR MAGNETIC RANDOM ACCESS MEMORY

This application is a divisional of application Ser. No. 10/828,162, filed Apr. 21, 2004, now U.S. Pat. No. 6,917, 534, which is a divisional of application Ser. No. 10/422, 850, filed Apr. 25, 2003, now Pat. No. 6,856,532, which is a divisional of application Ser. No. 09/938,722, filed Aug. 27, 2001, now Pat. No. 6,597,600, the entirety of each of which is hereby incorporated by reference.

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to the field of resistor-based memory circuits. More particularly, it relates to a method for precisely regulating the voltage applied across a resistive memory element during sensing.

2. Description of the Related Art

FIG. 1 shows one example of a resistor based memory. The memory includes a memory cell array 8 having a plurality of row lines 10 arranged in normal orientation to a plurality of column lines 12. Each row line is connected to each of the column lines by a respective resistor 14.

A Magnetic Random Access Memory (MRAM) is one approach to implementing a resistor based memory. In an MRAM, each resistive memory cell includes a magnetizable film. The resistance of the cell varies, depending on the magnetization state of the film. Logical data can be stored by magnetizing the film of particular cells so as to represent the logic states of the data. One resistance value, e.g., the higher value, may be used to signify a logic "HIGH" while the other resistance value, e.g., the lower value, may be used to signify a logic "LOW". The stored data can be read by measuring the resistance of the cells, and interpreting the resistance values thus measured as logic states of the data.

For MRAM sensing purposes, the absolute magnitude of resistance need not be known; only whether the resistance is above or below a value that is intermediate to the logic high and logic low values. Nonetheless sensing the logic state of an MRAM memory element is difficult because the technology of the MRAM device imposes multiple constraints. In a typical MRAM device an element in a high resistance state has a resistance of about 1 MΩ. An element in a low resistance state has a resistance of about 950 KΩ. The differential resistance between a logic one and a logic zero is thus about 50 KΩ, or 5% of scale. Rapidly distinguishing a 5% resistance differential on a scale of 1 MΩ with a minimum of circuitry is problematic.

Resistance is measured using Ohm's Law which holds that resistance is equal to the voltage across a resistor divided by the current through the resistor. Generally one parameter is held constant while the other is measured. In MRAM applications voltage is typically held constant while current is measured. As a result, the quality of an MRAM resistance measurement depends in large part upon the ability to regulate the voltage applied across a resistive memory element during sensing.

Where a stabilized voltage is required, it is known to use a voltage follower circuit constructed by feeding back an output signal of a differential amplifier to an inverting input of the amplifier, and connecting a reference voltage to the non-inverting input of the amplifier. FIG. 2 shows one embodiment of a conventional voltage follower in block diagram form. A voltage follower exhibits a voltage gain of about 1, high input impedance, and low output impedance.

A voltage follower circuit might thus be used to apply a voltage across a resistive memory element to sense the resistance of the resistor.

In practice, a conventional differential amplifier, such as might be found in a memory device, has offsets that affect the voltage across the memory cell. If an amplifier with an offset is used to provide a voltage across a MRAM resistive memory element for sensing purposes, the presence of the voltage offset in the differential amplifier reduces the accuracy of the voltage applied across the memory cell, and consequently the precision with which the logic state of the cell is read. Therefore, there is a need for an improved voltage source circuit that is readily implemented on an integrated circuit, that requires few components, that operates at high speeds, and that provides a highly accurate and stable voltage output and a current output appropriate to support MRAM memory element sensing.

BRIEF SUMMARY OF THE INVENTION

The present invention provides a method and apparatus for measuring the resistance of a resistive memory element. The resistance is measured by applying a controlled voltage across a resistive memory element and ascertaining the level of current that consequently flows through the resistive memory element. According to the present invention, an improved differential amplifier, including a compensation circuit, is used in a feedback configuration to set a standard voltage across a resistive memory element. The compensation circuit reduces the effect of differential amplifier offset and yields a more precise standard voltage across the resistive memory element.

In one aspect, the invention includes a memory element voltage supply including a transistor with a gate adapted to control an electrical current through the transistor in relation to a voltage applied to the gate. The transistor also includes a source (or drain depending on device polarity) operatively connected to the resistive memory device. The voltage supply includes a differential amplifier with a non-inverting input operatively connected to a source of a reference voltage, an inverting input, a first output switchingly connected to the gate of the transistor, and a second output. The supply further includes a compensation amplifier with a third input adapted to receive and store a first compensation voltage, a third output operatively connected to the first output, and a fourth output operatively connected to the second output. Also included is a feedback line including a switch adapted to switchingly connect the second input to the source (or drain) of the transistor.

In operation the voltage supply first enters a calibration phase. During the calibration phase, a first compensation voltage is stored at the third input of the compensation amplifier. Generally, this third input includes a capacitor which is charged to store the first compensation voltage. The compensation voltage stored reflects the magnitude of an offset voltage that exists in the differential amplifier when no differential voltage is applied across its inputs; that is, the compensation voltage reflects an error that exists in the output of the differential amplifier. After the calibration phase, the voltage supply enters a measurement phase. In the measurement phase the error voltage, stored on the capacitor, is used as an input to the compensation amplifier. The resulting output of the compensation amplifier counteracts the erroneous offset voltage that would otherwise be included in the output of the differential amplifier. As a result of this corrective action, the output of the differential amplifier is more accurate, and a more precise measurement may

be made of the resistance of the resistive memory element than would otherwise be possible.

These and other aspects and features of the invention will be more clearly understood from the following detailed description which is provided in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 shows a conventional magnetic random access memory array in electrical schematic form;

FIG. 2 shows a conventional voltage follower circuit including a differential amplifier in block diagram form;

FIG. 3 shows a portion of a magnetic random access memory device according to one aspect of the invention in electrical schematic form;

FIG. 4 shows a portion of a magnetic random access memory device according to one aspect of the invention including a sensing circuit and sneak resistance;

FIG. 5 shows a conventional voltage follower circuit including a differential amplifier and a transistor for applying a sensing voltage to a resistive memory element;

FIG. 6 shows a conventional circuit for a differential amplifier in electrical schematic form;

FIG. 7 shows a circuit for a differential amplifier according to one aspect of the invention including components for offset voltage compensation;

FIG. 8 shows, in block diagram form, a circuit according to one aspect of the invention for applying a standard voltage across a resistive memory element;

FIG. 9 shows, in block diagram form, the configuration of a circuit according to one aspect of the invention during calibration phase;

FIG. 10 shows, in block diagram form, a configuration of a circuit according to one aspect of the invention during measurement phase;

FIG. 11 shows, in block diagram form, a computer system incorporating a digital memory device including a compensated voltage source according to the present invention.

DETAILED DESCRIPTION OF THE INVENTION

FIG. 3 shows a resistive memory device according to one aspect of the invention. In the embodiments illustrated herein the resistive memory is referred to as MRAM memory; however, the invention is applicable to any type of resistance memory and is not limited to MRAM memory. The device includes an array 16 of Magnetic Random Access Memory (MRAM) elements, a plurality of electrically conductive row lines 10, and a plurality of electrically conductive column lines 12. Each row line is connected to each of the plurality of column lines by a respective MRAM resistive element 14. A plurality of switches 18, typically implemented as transistors, are each switchingly connected between one of the row lines and a first source of constant potential (ground) 20. A plurality of sensing circuits 22 are respectively connected to the plurality of column lines 12. Each sensing circuit 22 includes a source of constant electrical potential (V_A). According to the invention, the precision of this source of constant electrical potential (V_A) is improved with a compensation circuit.

A separate plurality of pull-up voltage sources 24 are respectively connected to each of the plurality of row lines 10. These supply voltage (V_A) to the row lines 10. These pull-up voltage sources 24 serve to maintain the ungrounded row lines at array voltage (V_A), thereby preventing leakage

current through so-called sneak resistance. Optionally, the voltage compensation method of the present invention may be applied to the plurality of pull-up voltage sources 24 attached to the row lines 10 respectively.

In operation, an exemplary switch 18, such as switch 26 associated with a particular row line 28, is closed so as to bring that row line to ground potential and a particular column line 12, for example column line 30, is used by a respective sensing circuit 32 to read the resistance value of resistor 34.

FIG. 4, shows the resulting electrical circuit for the relevant portion 36 of the memory array when row 28 and column 30 are activated. As shown, memory element 34 is connected between a grounded row line 28 and a particular column line 30. Also connected to the column line 30 are a plurality of other resistive memory elements (e.g., elements 38, 40, 42, 44, 46) each of which is connected at its opposite end to a source of electrical potential (V_A) 24 through a respective row line 10. In addition, a respective sensing circuit 32 is connected to the column line 30. The sensing circuit 32 includes a voltage supply, according to the present invention, that maintains the column line 30 at electrical potential (V_A). The other resistive memory elements (those tied to ungrounded row lines) 38, 40, 42, 44, 46, form an equivalent resistance referred to as earlier as sneak resistance. The effective resistance of the sneak resistance is small. A typical value for sneak resistance might be one KΩ. Nevertheless, because both ends of each ungrounded resistor are ideally maintained at the same potential (here V_A), net current flow through the sneak resistance is desirably nearly zero. Precise voltage regulation across the sneak resistance is therefore important, since any voltage differential across the sneak resistance results in an unwanted current flow through the sneak resistance that reduces measurement precision and increases power consumption and thermal losses. In contrast, a measurable current desirably flows through the grounded resistive memory element 34. This current allows measurement of the resistance of the memory element 34 by the sensing circuit 32.

FIG. 5 shows a conventional circuit 50 for applying a sensing voltage across a resistive memory element. A differential amplifier 52 is provided, including a non-inverting input 54, an inverting input 56, and an output 58. Also shown are supply 60 and ground 62 connections of the differential amplifier connected to a source of supply (VCC) 64 and a ground 20 respectively (note that in an alternative embodiment, the differential amplifier might be connected for power between two non-ground potentials). The non-inverting input 54 of the differential amplifier is operatively connected to a source of a reference voltage (V_A) 66. The output 58 of the differential amplifier is operatively connected to a gate 68 of a transistor 70. As would be understood by one of skill in the art, transistors of various polarities may be employed, and the output signal of the differential amplifier inverted accordingly. As shown, an enhancement mode NMOS field effect transistor is used. A drain 78 of the transistor is connected to a power supply (VCC) 64 and a source 82 of the transistor is connected to a column line 30 which is, in turn, connected to one end of a resistive memory element 34. The other end of the resistive memory element 34 is connected to a row line 28 that is switchingly connected to a ground potential 20 by a switch 26. The column line 30 is also connected to the inverting input 56 of the differential amplifier 52 and to the sneak resistance collectively indicated as 84. In operation an output signal of the differential amplifier controls the gate 68

of the transistor to maintain a voltage ideally equal to the reference voltage (V_A) **66** on the column line **30**.

In practice, offsets within the differential amplifier result in a voltage at the column line **30** that deviates from that of the reference voltage **66**. The offset within the differential amplifier is represented in FIG. **5** by a voltage **86** applied to or subtracted from the non-inverting input **54** of the differential amplifier.

FIG. **6** shows a schematic representation of a circuit **88** of a conventional differential amplifier used as differential amplifier **52**. The circuit includes an output connection **58** an inverting transistor **90** including a gate **92** connected to an inverting input **56** and a non-inverting transistor **94** including a gate **96** connected to a non-inverting input **54**. The drain **98** of the non-inverting transistor **94** is operatively connected to the source of supply voltage (VCC) **64**. The drain **100** of the inverting transistor **90** is operatively connected to the output **58** of the differential amplifier, and also to one end **102** of a pull-up resistor **104**. The other end **106** of the pull-up resistor is connected to the source of supply (VCC) **64**. First **108** and second **110** source connections of the inverting **90** and non-inverting **94** transistors respectively are connected in common to a first terminal **112** of a current source **114**. A second terminal **116** of the current source **114** is connected to ground **20**. Also shown is a voltage source **86** representing, a +/− offset within the differential amplifier **88**. Note that although offset voltage is represented throughout the present disclosure as a lumped voltage source, this is a simplified representation. Actually offsets may arise from a variety of causes and components distributed within the electrical components of the resistance measurement voltage supply.

FIG. **7** shows a compensated differential amplifier circuit according to one aspect of the invention. The circuit includes an operative connection to a source of supply voltage (VCC) **64**, a pull-up resistor **110** and an output connection **112**. The output connection **112** is connected to one end **114** of the pull-up resistor **110**. The other end **116** of the pull-up resistor is operatively connected to the source of supply voltage (VCC) **64**. The amplifier also includes an inverting transistor **118** with a gate **120** connected to an inverting input **122** and a non-inverting transistor **124** including a gate **126** connected to a non-inverting input **128**. A drain **130** of the inverting transistor **118** is connected to the output **112** of the amplifier. A drain **132** of the non-inverting transistor **124** is operatively connected to the source of supply voltage (VCC) **64**. Optionally, the drain **132** of the non-inverting transistor may be available on a complementary output. First **134** and second **136** source connections of the inverting **118** and non-inverting **124** transistors respectively are connected in common to a first terminal **138** of a first current source **140**. A second terminal **142** of the first current source **140** is connected to ground **20**. Also shown is a voltage source **144** representing, a +/− offset within the differential amplifier **146**. As discussed above, although offset voltage **144** is shown as a lumped voltage source, this is a simplified representation. Offsets at the output of the differential amplifier **146** may result from various causes such as component asymmetry within the differential amplifier **146**.

According to one aspect of the invention, the amplifier **146** includes an offset compensation circuit **148** in the form of a second differential amplifier. The offset compensation circuit **148** includes a first compensation transistor **150** and a second compensation transistor **152**. The drain **154** of the first compensation transistor **150** is operatively connected to the drain **130** of the inverting transistor **118**, and consequently to the output **112** of the differential amplifier **146**.

The drain **156** of the second compensation transistor **152** is operatively connected to the drain **132** of the non-inverting transistor **124**. A source connection **158** of the first compensation transistor **150** and a source connection **160** of the second compensation transistor **152** are connected in common to a first terminal **162** of a second current source **164**. A second terminal **166** of the second current source **164** is connected to ground **20**. A gate **168** of the first compensation transistor **150** is connected to a first terminal **170** of a first compensation capacitor **172**. A second terminal **174** of the first compensation capacitor **172** is connected to ground **20**. A gate **176** of the second compensation transistor **152** is connected to a first terminal **178** of a second compensation capacitor **180**. A second terminal **182** of the second compensation capacitor **180** is connected to ground **20**.

FIG. **8** shows an operational connection **200** of the differential amplifier of FIG. **7** according to one aspect of the invention. As shown in FIG. **8**, the amplifier **146** of FIG. **7** is represented as an amplifier block **202** and includes the portion of compensation circuit **148** identified in FIG. **7** as **186**. The first **172** and second **180** compensation capacitors and their mutual connection to ground **20**, shown in FIG. **7** as portions **184**, **188** of FIG. **7** are shown externally in FIG. **8**. According to the invention, the output **112** of the differential amplifier **202** is connected through a switch **204** to a gate **68** of a control transistor **70**. The control transistor includes a drain **78** connected to a power supply (VCC) **64** and a source **82** connected to a column line **30** of a resistive memory integrated circuit device. The column line **30** is connected to one terminal **206** of a resistive memory element **34**. The resistive memory element includes a second terminal **208** connected to a row line **28** that is switchingly connected to ground **20** through a switch **26**. The differential amplifier **202** includes a non-inverting input **128** operatively connected to a source of a reference voltage **66**. The amplifier **202** also includes an inverting input **122** connected by means of a switch **210** to the same reference voltage (V_A) **66**. The inverting input **122** also is switchingly connected by means of a second switch **212** to the column line **30**. The first terminal **170** of the first compensation capacitor **172** is also switchingly connected by means of a further switch **214** to the output **112** of the differential amplifier **202**. The first terminal **178** of the second compensation capacitor **180** is switchingly connected by means of a further switch **216** to the reference voltage source (V_A) **66**. As noted above, the second terminals **174** and **182** of the first compensation capacitor **172** and of the second compensation capacitor **180** respectively are connected to ground **20**.

A control circuit **218**, which may be external to the amplifier **202**, controls switches **204**, **210**, **212**, **214**, **216** to switch the amplifier between a calibration mode configuration, and a resistive element measurement mode configuration. The control circuit **218** includes a first phase output **220** operatively connected to switches **210**, **214**, and **216**. The control circuit **218** includes a second phase output **222** operatively connected to switches **204** and **212**.

In operation, the differential amplifier circuit shown in FIG. **8** switches between two modes; a calibration mode, or a resistance measurement mode.

In a calibration mode, switches **204** and **212** are open; switches **210**, **214** and **216** are closed. Generally speaking, the switches **204**, **210**, **212**, **214**, and **216** (FIG. **8**) are implemented as transistors, and are operated under the control of control circuitry **218**. Prior to sensing the stored value of a resistive memory element, the control circuitry **218** places the differential amplifier **202** in a calibration mode by opening switches **204** and **212**, and closing

switches **210**, **214**, and **216**. FIG. **9** shows the resulting connection of the differential amplifier of the invention. The non-inverting **128** and inverting **122** inputs of the differential amplifier **202** are connected together and held at reference potential (V_A) **66**. The first terminal **178** of the second capacitor **180** is also held at reference potential (V_A) **66**. In this configuration, there is no differential voltage across the inputs **128**, and **122**, of the differential amplifier. Any voltage that appears on the output **112** is therefore an offset voltage and is, by definition, undesirable. Because the circuit is in a calibration mode configuration, this offset voltage is fed back through switch **214** to the first compensation capacitor **172**. The first compensation capacitor **172** is charged by the differential amplifier until the voltage on the capacitor **172** is equal to the offset voltage at the output **112** of the differential amplifier **146**. Thereafter, the control circuitry places the amplifier in the resistance measurement mode. Once the circuit is returned to measurement mode, this stored voltage acts to produce an inverse offset that negates the offset that would otherwise be present at the output **112** of the amplifier **202**.

FIG. **10** shows the differential amplifier **202** connected for use in a resistance measurement mode. In resistance measurement mode, switches **210**, **214**, and **216** are open, and switches **204** and **212** are closed. The reference voltage (V_A) **66**, plus the offset voltage **144** are applied to the non-inverting input **128** of the differential amplifier **202**. The first compensation input **224** corresponds to the gate **168** of the first compensation transistor **150**. Accordingly, the pre-charged first compensation capacitor **172** applies a stored voltage of (V offset) to the gate **168** of the first compensation transistor **150** (FIG. **7**). The second compensation capacitor **180** exhibits pre-stored charge (V_A) that is applied to a second compensation input **226** of the differential amplifier. The second compensation input **226** corresponds to the gate **176** of the second compensation transistor **152**. Accordingly, the pre-stored voltage (V_A) is applied to the gate **176** of the second compensation transistor **152** (FIG. **7**). As a result, the first **150** and second **152** compensation transistors shunt current from the drains of the inverting **118** and non-inverting **124** transistors respectively to ground **20**. This shunt current is just enough to adjust the voltage that appears on the output **112** of the amplifier **146** so as to substantially eliminate voltage offset from that output.

The combination of the compensated differential amplifier and the transistor **70** act to maintain a voltage (V_A) on column line **30**, and accordingly across the resistive memory element **34** during measurement with minimized errors due to offsets in the differential amplifier **202**. If the voltage on the column line **30** drops below (V_A), negative feedback into the inverting input **122** of the differential amplifier results in a signal to the gate **68** of the transistor that increases current flow through the transistor and returns the voltage of the column line **30** to voltage (V_A).

In one aspect, the control circuit **218** acts to place the amplifier in calibration mode at the beginning of every read cycle. In a variation, the control circuitry places the amplifier in calibration mode prior to a first read, and then returns the amplifier to calibration mode only after a predefined number of read cycles. In a further variation, the control circuit **218** places the amplifier in calibration mode prior to a first read cycle, and then returns the amplifier to calibration mode only after a definite value of voltage offset is sensed on the output **112**.

FIG. **11** shows a computer system **230** including a memory **232** including one or more resistive memory devices which are constructed to include the invention as

described and illustrated with reference to FIGS. **7–9**. The computer **230**, as shown includes a central processing unit (CPU) **234**, for example a microprocessor, that communicates with one or more input/output (I/O) devices **236** over a bus **238**. The computer system also includes a peripheral device such as disk storage **240** and a user interface **242**. It may be desirable to integrate the processor **234** and memory **232** on a single integrated circuit device. Other processing systems in which the invention, in different embodiments may be employed include radio systems, television systems, wireless, wired, and optical voice and data networks, global positioning system receivers, and other systems where digital data storage is required.

While preferred embodiments of the invention have been described in the illustrations above, it should be understood that these are exemplary of the invention and are not to be considered as limiting. Additions, deletion, substitution, and other modifications can be made without departing from the spirit or scope of the present invention. Accordingly, the invention is not to be considered as limited by the foregoing description but is only limited by the scope of the appended claims.

The invention claimed is:

1. A method of operating a resistive memory integrated circuit comprising:

during a first time period disconnecting a differential amplifier from an array of memory elements, of said memory integrated circuit, and compensating said differential amplifier to minimize output voltage offset of said differential amplifier; and

during a second time period, subsequent to said first time period, connecting said differential amplifier to said array of memory elements of said memory integrated circuit and measuring a value of a resistive memory element of said array,

wherein said compensating step comprises connecting a first and a second signal input of said differential amplifier to a nonzero reference voltage.

2. A method according to claim **1** wherein said reference voltage is generated from a common voltage source.

3. A method according to claim **1** wherein:

during said first time period, a first capacitor connected to a first compensation input of said differential amplifier is charged to a ground potential, and a second capacitor connected to a second compensation input of said differential amplifier is charged to a compensation potential, and

during said second time period said first and second capacitors maintain said respective first and second compensation inputs at said ground and compensation potentials respectively.

4. A method of operating a resistive memory integrated circuit, the method comprising:

calibrating a sensing voltage circuit to reduce a voltage offset of said sensing voltage circuit; and

applying a sensing voltage across a resistive memory element of said integrated circuit to determine a resistance level of said resistive memory element,

wherein said calibrating step comprises connecting a first and a second signal input of a differential amplifier to a nonzero reference voltage.

5. The method of claim **4**, wherein said act of calibrating further comprises:

determining a level of said offset voltage; and

generating an inverse offset to substantially negate said offset voltage.

6. The method of claim **4**, wherein said act of calibrating further comprises:

   disconnecting an output of a differential amplifier portion of said sensing voltage circuit;

   determining that an offset voltage is present at said output of said differential amplifier portion of said sensing voltage circuit;

   feeding said offset voltage present at said output of said differential amplifier portion of said sensing voltage circuit to a compensation capacitor of said sensing voltage circuit; and

   charging said compensation capacitor with said differential amplifier until a voltage stored by said compensation capacitor is substantially equal to said offset voltage.

7. A method of operating a resistive memory integrated circuit comprising:

   during a first time period disconnecting a differential amplifier from an array of memory elements, of said memory integrated circuit, and compensating said differential amplifier to minimize output voltage offset of said differential amplifier;

   during a second time period, subsequent to said first time period, connecting said differential amplifier to said array of memory elements of said memory integrated circuit and measuring a value of a resistive memory element of said array; and

   during said second time period, holding a column line connected to said memory element at a predetermined voltage using a voltage circuit.

8. A method of operating a resistive memory integrated circuit, the method comprising:

   calibrating a sensing voltage circuit to reduce a voltage offset of said sensing voltage circuit;

   applying a sensing voltage across a resistive memory element of said integrated circuit to determine a resistance level of said resistive memory element; and

   holding a column line connected to said memory element at a predetermined voltage using a voltage circuit while applying said sensing voltage.

* * * * *